

### **isc** Silicon PNP Power Transistor

## **MJD350**

### DESCRIPTION

- Collector–Emitter Sustaining Voltage–
  - : V<sub>CEO(SUS)</sub> = -300 V(Min)
- · Low Collector Saturation Voltage-
- : V<sub>CE(sat)</sub> = -1.0V(Max.)@ I<sub>C</sub>= -50mA
- DPAK for Surface Mount Applications
- Complement to Type MJD340
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

VALUE UNIT

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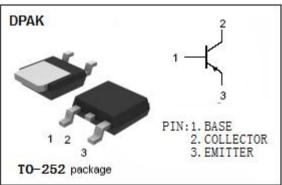
#### **APPLICATIONS**

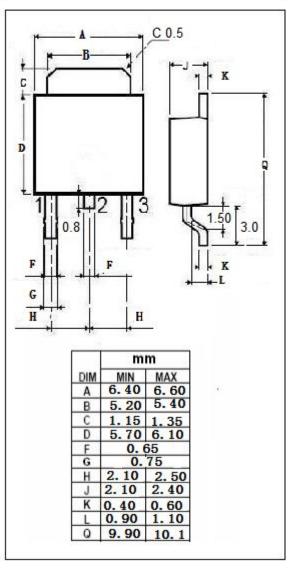
SYMBOL

• Designed for line operated audio output amplifier, switchmode power supply drivers and other switching applications.

PARAMETER

ABSOLUTI	E MAXIMUM RATINGS(Ta=25°C)





STWBOL	FARAMETER			UNIT				
V <sub>сво</sub>	Collector-Base Voltage	-300		V				
V <sub>CEO</sub>	Collector-Emitter Voltage	-300		V				
V <sub>EBO</sub>	Emitter-Base Voltage	-3		V				
lc	Collector Current-Continuous	-0.5		А				
Ісм	Collector Current-Peak	-0.75		А				
Pc	Collector Power Dissipation $T_c=25^{\circ}C$	15		W				
	Collector Power Dissipation $T_a=25^\circ\mathbb{C}$	1.56						
Ti	Junction Temperature	150		°C				
T <sub>stg</sub>	Storage Temperature Range	-65~150		°C				
THERMAL	THERMAL CHARACTERISTICS							
SYMBO L	PARAMETER		МАХ	UNIT				
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case			°C/W				
R <sub>th</sub> j-a	Thermal Resistance, Junction to Ambient			°C/W				



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### ELECTRICAL CHARACTERISTICS

#### $T_c$ =25 $^{\rm C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -1.0mA; I <sub>B</sub> = 0	-300		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -1.0mA; I <sub>E</sub> = 0	-300		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -1.0mA; I <sub>C</sub> = 0	-3		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -50mA; I <sub>B</sub> = -5mA		-1.0	V
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = -300V; I <sub>E</sub> = 0		-0.1	mA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = -3V; I <sub>C</sub> = 0		-0.1	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -50m A ; V <sub>CE</sub> = -10V	30	240	

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